Role of oxygen vacancies in the magnetic and dielectric properties of the high-dielectric-constant system CaCu$_3$Ti$_4$O$_{12}$: An electron-spin resonance study

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We report experiments of electron spin resonance (ESR) of Cu$^{2+}$ in polycrystalline samples of CaCu$_3$Ti$_4$O$_{12}$ post-annealed in different atmospheres. After being synthesized by solid state reaction, pellets of CaCu$_3$Ti$_4$O$_{12}$ were annealed for 24 h at 1000 °C under air, Ar or O$_2$. Our temperature dependent ESR data revealed for all samples nearly temperature independent g value (2.15(1)) and linewidth for $T>T_N=25$ K. However, the values of ESR linewidth are strongly affected by the oxygen content in the sample. For instance, argon post-annealed samples show a much larger linewidth than the O$_2$ or air post-annealed samples. We attribute this broadening to an increase of the dipolar homogeneous broadening of the Cu$^{2+}$ ESR lines due to the presence of oxygen vacancies which induce an $S=1/2$ spin inside the TiO$_6$ octahedra. Correlation between a systematic dependence of the ESR linewidth on the oxygen content and the high dielectric constant of these materials is addressed. Also, ESR, magnetic susceptibility, and specific heat data for a single crystal of CaCu$_3$Ti$_4$O$_{12}$ and for polycrystals of CdCu$_3$Ti$_4$O$_{12}$ are reported.

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I. INTRODUCTION

Recently, the body-centered perovskite-related compounds ACu$_3$Ti$_4$O$_{12}$ have attracted much attention due to the extremely high dielectric constant $\varepsilon_0 \sim 10^4$ reported for ceramic and single crystals of the specimen with $A=$Ca.$^{1-3}$

High dielectric constant materials are very important for technological applications as in the case of capacitive memory devices. Aside from its potential technological application, the fundamental physics responsible for such enhanced dielectric constant has interested theorists and experimentalists working in this field. However, a definitive scenario to explain the large dielectric constant of CaCu$_3$Ti$_4$O$_{12}$ has not yet been established. Although a large $\varepsilon_0$ could have an intrinsic origin associated to Ca displacements, distortions of the TiO$_6$ octahedra, or small concentration of defects that disrupt the braced lattice, several reports have raised doubts about the intrinsic origin of such high value of $\varepsilon_0$.\(^4\) For instance, Lunkenheimer et al. have proposed that the origin of the high value of the dielectric constant of CaCu$_3$Ti$_4$O$_{12}$ is simply an extrinsic effect associated with Maxwell-Wagner-type depletion layers at the sample contacts or at grain boundaries. On the other hand, subsequent studies\(^5\) have shown that the addition of a buffer between the sample and the contacts has no influence on the large value of $\varepsilon_0$, indicating that the contacts alone cannot be responsible for these large values. Nevertheless, these studies relying on infrared measurements in CaCu$_3$Ti$_4$O$_{12}$ and CdCu$_3$Ti$_4$O$_{12}$ suggested that the giant measured dielectric constant of CaCu$_3$Ti$_4$O$_{12}$ is, at least in part, caused by an internal barrier layer capacitance (IBLC) effect.\(^5,6\) This IBLC would be a consequence of the existence of semiconducting regions in the sample separated by insulating barriers.\(^5\) However, this scenario, based on the IBLC effect, cannot fully explain the rapid suppression of $\varepsilon_0$ that occurs at low temperatures for CaCu$_3$Ti$_4$O$_{12}$, and also, the large decrease in the value of $\varepsilon_0$ caused by chemical substitution at the A =Ca site. Besides all the efforts trying to understand the origin of the giant dielectric constant, significant experimental work has been devoted to explore the evolution of the high dielectric constant of these materials as a function of chemical substitution (for example Ca-site and/or Ti-site doping) and sample preparation methods.\(^7-10\) Although $\varepsilon_0$ has been found to strongly depend on these parameters, to establish a clear systematic correlation between a sample with certain characteristic (for instance, growth temperature and/or amount of doping) and its value of dielectric constant remains a challenge.

The magnetic susceptibility and electron spin resonance (ESR) experiments done in CaCu$_3$Ti$_4$O$_{12}$ are consistent with an antiferromagnetic ordering of the Cu$^{2+}$ ions at $T_N=25$ K.\(^7,8,11\) Above $T_N$, Raman scattering experiments have revealed short range magnetic fluctuations that increase with cooling following a $T^{-1}$ dependence. The behavior of these fluctuations as a function of temperature was suggested to be related to the dramatic increase of $\varepsilon_0$ at high temperature.\(^1,11\)
It is well established that for other oxides materials, variation in the oxygen stoichiometry gives rise to many complex and interesting behaviors. Examples are the colossal magneto-resistance manganites (CMR) and the high-\(T_C\) superconductor (HTSC) compounds.\textsuperscript{12-15}

Here, we report measurements of ESR, magnetic susceptibility, specific heat, and dielectric constant in polycrystalline samples of CaCu\(_3\)Ti\(_4\)O\(_{12}\) and CdCu\(_3\)Ti\(_4\)O\(_{12}\) post-annealed in different atmospheres and in a CaCu\(_3\)Ti\(_4\)O\(_{12}\) single-crystal grown in an image furnace. Our \(T\)-dependent ESR data show for all the samples, basically a \(T\)-independent \(g\)-value (2.15(1)) and linewidth for \(T \gg T_N \approx 25\) K. But the values of the ESR linewidth and dielectric constant strongly depend on the oxygen content of the sample. Instead, the \(g\) value and the ordering temperature are unchanged by the annealing. Our results allowed us to conclude that the high value of the dielectric constant is dominated by an extrinsic IBLC effect. However, our data also indicated that there may be an intrinsic component of this large dielectric constant associated with the presence of oxygen vacancies, presumably in the TiO\(_6\) octahedra, that disrupts the bracing in the lattice. Unfortunately, from our results we cannot separate these two contributions.

II. EXPERIMENT

Polycrystalline samples of (Ca, Cd)Cu\(_3\)Ti\(_4\)O\(_{12}\) were grown by solid state reaction starting with CaCO\(_3\) or CdO, CuO, and TiO\(_2\). Stoichiometric powders of Ca base samples were heated at 900 °C for 12 h and then reheated at 1100 °C for 12 h more. A similar process was carried out for the Cd samples, but at 800 and 950 °C, for 12 h each, respectively. Finally, the samples were post-annealed for 24 h at 1000 °C for the Ca-based materials and at 900 °C for the Cd samples. A group of samples was reground after being heated for the first time and pelletized before the second heat treatment, and a second group was pelletized before the post-annealing. A last set of samples was not pelletized during the whole growth process (first, second, and post-annealing treatments) to allow for larger surface interchange. Some samples of this set were pelletized afterwards at room-\(T\) for specific measurements. The different sample growth treatments had the goal to obtain samples of different granularity (grain sizes and boundaries). The CaCu\(_3\)Ti\(_4\)O\(_{12}\) single crystal was grown by a traveling-solvent floating zone method using an image furnace as described previously.\textsuperscript{11} The CaCu\(_3\)Ti\(_4\)O\(_{12}\) structure type and phase purity were confirmed by x-ray powder diffraction. For the studied samples, no measurable changes in the lattice parameters caused by annealing was observed. The presence of secondary phases were estimated to be less than 1%. The set of temperatures, heating, and annealing times were chosen to maintain sample integrity. A moderate departure from the listed annealing temperatures and times gave rise to a sample deterioration, mainly with a TiO\(_2\) phase segregation. The ESR experiments were carried out in a conventional Bruker ESR spectrometer using a TE\(_{102}\) room-\(T\) cavity for \(X\) band and split-ring cavity for \(Q\) band. The sample temperature was varied using a helium gas-flux temperature controller. Specific heat measurements were performed in a Quantum Design PPMS small-mass calorimeter that employs a quasi-adiabatic thermal relaxation technique. Magnetization measurements were made in a Quantum Design dc superconducting quantum interference device and dielectric constant was extracted from impedance measurements performed with a Hewlett-Packard model 4263B LCR meter in the frequency range of 100 Hz–100 kHz. Silver paint electrodes, annealed at 300 °C, were applied on opposing edges of the specimens. Contact contributions to the impedance were eliminated for each specimen using measurements for several electrode separations.\textsuperscript{18}

III. RESULTS

Figure 1 shows in the left-hand side the room-\(T\) \(X\)-band (\(\nu \approx 9.5\) GHz) ESR spectra fitted to a single Lorentzian line for several samples of (Ca, Cd)Cu\(_3\)Ti\(_4\)O\(_{12}\) as-grown and post-annealed under different conditions. This particular set of data belongs to powder samples that were not pelletized at all. The spectra show (for \(T > 40\) K) a single resonance with a \(g\) value of 2.15(1) for all the samples. A large dependence on the atmosphere of the post-annealing treatment was found for the ESR linewidth for these samples. The broadest line-widths were observed for the polycrystalline argon annealed and the single crystals of CaCu\(_3\)Ti\(_4\)O\(_{12}\). Although not studied in detail, similar post-annealing linewidth behavior was observed for the CdCu\(_3\)Ti\(_4\)O\(_{12}\) polycrystals (not shown). The \(Q\)-band (\(\nu \approx 34\) GHz) spectra of the as-grown and argon post-annealed polycrystals, and the single crystals of CaCu\(_3\)Ti\(_4\)O\(_{12}\) are shown on the right-hand side of Fig. 1. The \(g\)-value and the linewidth are frequency independent, i.e., the linewidths are not inhomogeneously broadened by a measurable \(g\)-value anisotropy and/or distribution. The ESR spectra intensity for all samples were compared to the intensity of a standard strong pitch with a known number of spins. From this analysis we found that for all samples the observed resonance comes from \(\sim 100\%\) of the Cu\(^{2+}\) ions.
The $T$-dependence of the ESR linewidth for the samples of Fig. 1 is shown in Fig. 2. For all samples, a nearly $T$-independent linewidth is observed for $T>40$ K, with a small broadening at high-$T$ (for $T\approx 200$ K), as previously reported.\cite{7,8} The weak $T$-dependence of the linewidth excludes the possibility of a Jahn-Teller distortion as being the origin of the dramatic increase of $\varepsilon_0$ observed above $\sim 100$ K.\cite{11} Although the $T$-dependence of the ESR linewidth is similar for all samples, there is a $T$-independent contribution to the linewidth ($\Delta H_0$) that strongly depends on the post-annealing atmosphere. For all temperatures (see Fig. 1), the argon post-annealed samples present broader linewidth than the air or oxygen annealed samples of CaCu$_3$Ti$_4$O$_{12}$. For the single crystal, the ESR linewidth is about one order of magnitude larger than that of the as-grown polycrystalline sample of CaCu$_3$Ti$_4$O$_{12}$.

Figure 3 shows the dramatic influence on the ESR spectra of the post-annealing treatment (air, Ar, or O$_2$) for the powder samples of CaCu$_3$Ti$_4$O$_{12}$ from the same set of samples of Figs. 1 and 2. While for samples annealed in air and O$_2$, the linewidth remains as narrow as for the as-grown samples $\Delta H \approx 40$ Oe, the argon annealed samples present a much broader ESR linewidth, $\Delta H \approx 150$ Oe.

Thus, the Cu$^{2+}$ ESR linewidth is strongly dependent on the oxygen content. We associate the line broadening with the presence of oxygen vacancies caused by the argon annealing. The broadening of the Cu$^{2+}$ ESR linewidth for the argon post-annealed samples can be partially reverted when the same powder is re-annealed in O$_2$ (see Fig. 3). In contrast, the $g$ value was found to be independent of the post-annealing treatments. It is important to point out that similar ESR linewidth behavior (Figs. 1–3) was observed for all groups of samples described in Sec. II. However when the post-annealing process was done on pellets of CaCu$_3$Ti$_4$O$_{12}$, the linewidth changes as function of the atmosphere were much less dramatic, presumably due to a smaller effective surface for O$_2$ exchange.

Magnetic susceptibility measured as a function of temperature at $H=1$ kOe for an as-grown CdCu$_3$Ti$_4$O$_{12}$ sample and three samples of CaCu$_3$Ti$_4$O$_{12}$ (as-grown, single crystal, and argon-annealed) is shown in Fig. 4. For the polycrystalline samples, this particular set of data belongs to the group of samples that were pelletized at room-$T$ only after the post-annealing treatment. However, as discussed in the following, the low-$T$ magnetic susceptibility is only affected by the post-annealing treatment and not by the pelletizing process itself.

An antiferromagnetic phase transition is observed at $T_N \approx 25$ K for all the samples of CaCu$_3$Ti$_4$O$_{12}$ and at $T_N \approx 29$ K for the CdCu$_3$Ti$_4$O$_{12}$. At first glance, one can see the development of a low-$T$ Curie tail for the argon post-annealed and the single crystal samples of CaCu$_3$Ti$_4$O$_{12}$. The $T$-dependence of the magnetic susceptibility of the as-grown and single crystalline sample of CaCu$_3$Ti$_4$O$_{12}$ is in excellent agreement with the data reported in Refs. 8 and 11, respec-

FIG. 2. Cu$^{2+}$ ESR linewidth as a function of temperature for several samples of CaCu$_3$Ti$_4$O$_{12}$.

FIG. 3. X-band ESR spectra for several samples CaCu$_3$Ti$_4$O$_{12}$ after different post-annealing heat treatments.

FIG. 4. Temperature dependence of the magnetic susceptibility taken with an applied field $H=1$ kOe for select samples of ACu$_3$Ti$_4$O$_{12}$ (A=Ca and Cd) compounds.
From the high-\(T\) Curie-Weiss linear fits of the inverse of the magnetic susceptibility, we have extracted the following Curie constants for the Ca-based samples, all given in \((\text{emu}/(\text{moleCu Oe K}))\): \(4.70 \times 10^{-1}\) (as grown), \(4.48 \times 10^{-1}\) (argon annealed), and \(4.64 \times 10^{-1}\) (single crystal). Assuming an Avogadro number of \(\text{Cu}^{2+}\) ions for the as-grown \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\), we have obtained an effective magnetic moment of 1.94(4) Bohr magnetons for \(\text{Cu}^{2+}\) in the as-grown \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) and \(\text{CdCu}_3\text{Ti}_4\text{O}_{12}\), and somewhat smaller \(\text{Cu}^{2+}\) effective moments for the argon annealed and single-crystal \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) samples. One may speculate that some \(\text{Cu}^{2+}\), \(S=1/2\), ions are missing in order to explain the decrease of the Curie constant for the argon annealed and single-crystal samples. One possibility is that the oxygen vacancies dope the material transforming some of the \(\text{Cu}^{2+}\) ions into non-magnetic \(\text{Cu}^{1+}\) and some of the \(\text{Ti}^{4+}\) ions into magnetic \(\text{Ti}^{3+}\) with \(S=1/2\). Support for such argument is given by the low-\(T\) Curie tail, observed for the argon annealed and single-crystal \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) samples, which may be attributed to \(\text{Ti}^{3+}\). A Curie-Weiss fitting of the tail for those samples yields a Curie constant of \(2.3 \times 10^{-2}\) and \(8.0 \times 10^{-3}\) (emu/(moleTi Oe K)) for argon annealed and single crystal samples, respectively. Note that, for the argon annealed and single crystal samples of \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\), the Curie constant, extracted from the high-\(T\) behavior plus that extracted from the Curie tail, is in good agreement with the Curie constant obtained for the as-grown \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\). In other words, the number of \(\text{Cu}^{2+}\) ions summed to the number of \(\text{Ti}^{3+}\) ions for argon annealed and single crystal samples of \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) is similar to the number of \(\text{Cu}^{2+}\) ions in the as-grown \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) sample. From the fit to the low-\(T\) Curie tail, we estimated about 5% of non-interacting \(S=1/2\) spins (oxygen vacancies) in the argon annealed and around 2% in the single crystal sample. The similarities between the data for the argon annealed polycrystals and the single crystal sample of \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) suggest that the \(\text{CaCu}_3\text{Ti}_4\text{O}_{12}\) single crystals grown by a traveling-solvent floating zone method\(^{11}\) are also oxygen deficient.

Figure 5 presents the low-\(T\) specific heat divided by \(T\) for the same set of samples of Fig. 4. Similar to the magnetic susceptibility data the macroscopic antiferromagnetic behav-

\[
\text{ACu}_3\text{Ti}_4\text{O}_{12} \quad \text{CaCu}_3\text{Ti}_4\text{O}_{12} \quad (\text{Pellets})
\]

\[
\begin{array}{ccc}
\text{A = Cd} & \text{A = Ca} & \text{A = Ca (Xtal)} & \text{A = Ca (Ar anneal.)} \\
\text{Ar post-anneal.} & \text{Air post-anneal.} & \text{O}_2 \text{ post-anneal.} \\
\text{O}_2 \text{ post-anneal. - pell. after post-anneal. at room-T} & \text{Air post-anneal. - pell. before sec, heat treat.} & \text{Ar post-anneal. - pell. before post-anneal.}
\end{array}
\]

\[
\text{FIG. 5. Specific heat per mole divided by temperature as a function of temperature for select samples of ACu}_3\text{Ti}_4\text{O}_{12} \ (\text{A} = \text{Ca and Cd}).
\]

\[
\text{FIG. 6. Frequency dependence of the dielectric constant } \varepsilon \text{ for several samples of CaCu}_3\text{Ti}_4\text{O}_{12} \text{ prepared and/or post-annealed in different conditions.}
\]
omentry strongly modifies the effective doping levels of the material which places the studied compound in different regions of its phase diagram. In the latter compounds, oxygen vacancies are responsible for trapping electrons or inducing distortions/strain that can dramatically affect the dielectric properties of those materials. When trapping electrons the oxygen vacancies defect can bind one or two electrons, giving rise to singly charged electrons the oxygen vacancies defect can bind one or two neutral F centers.

As we discussed in the previous section, we found a large broadening of the Cu2+ ESR linewidth for samples with oxygen vacancies and in order to understand how this broadening can result from them, different contributions to the ESR linewidth must be considered.

There are two types of ESR line broadening in solids: homogeneous and inhomogeneous broadening. Homogeneous ESR linewidth is inversely proportional to the so-called spin–spin relaxation time, $T_2$. It occurs when the magnetic resonance signal results from a transition between two levels of spins which are not sharply defined, but instead, are somewhat intrinsically broadened. The main contributions to homogeneous broadening are: (1) dipolar interaction between like spins, (2) spin-lattice interaction, (3) interaction with radiation field, (4) diffusion of excitation throughout the sample, and (5) motionally narrowing fluctuations of local fields.

On the other hand, an inhomogeneously broadened resonant line is one which consists of a spectral distribution of individual lines merged into an overall line or envelope. For instance, a distribution of local fields caused by unresolved fine and/or hyperfine structure, g-value anisotropy, strain distribution and/or crystal irregularities that exceed the natural linewidth $(2g^2/\gamma T_2)$, $\gamma$ is the gyromagnetic factor, will make the spins in various parts of the sample feel different field strengths. In this way the resonance will be artificially broadened in an inhomogeneous manner. In the cases of inhomogeneous broadening caused by g-value anisotropy and related strain distribution and/or crystal irregularities, the ESR linewidths are expected to increase as a function of magnetic field. From Fig. 1 we see that the Cu2+ ESR linewidth for ACu$_3$Ti$_4$O$_{12}$ (A=Ca and Cd) is field (band-frequency) independent, therefore, we can rule out these contributions as the origin of the observed Cu2+ ESR linewidth.

For the homogeneous broadening, the spin-lattice interaction is the most important contribution to the ESR linewidths and it becomes dominant when the spin-lattice relaxation time, $T_1$, is comparable to $T_2$. In this case, the ESR linewidth is generally frequency independent but it is strongly temperature dependent (direct, Orbach, Raman, and exchange relaxation processes) because it is ultimately coupled to the phonons. This behavior is in contrast to the nearly $T$-independent Cu2+ ESR linewidths observed for $T=40$ K in all our samples. Therefore, we conclude that spin-lattice relaxation cannot be the dominant mechanism responsible for the Cu2+ ESR linewidths in ACu$_3$Ti$_4$O$_{12}$ (A=Ca and Cd). Others sources for homogeneous broadening such as diffusion and motional narrowing process are unlikely to be present in our samples because the observed ESR lines arise from the Cu2+ ions that are fixed in the crystal lattice. Besides, there is no evidence for radiation field effects and the resonance line shapes are Lorentzian.

Therefore, the most probable homogeneous broadening mechanism present in our samples is the dipolar interaction between $S=1/2$ like spins. Van Vleck has treated in detail the homogeneous line broadening mechanism involving dipolar and exchange interactions. For a simple cubic lattice of like spins a dipolar interaction produce a linewidth $\Delta H = 2\rho g^2 \beta S(S+1)^{1/2}$, where $\rho$ is the density of spins/cm$^3$, $g$ is the g value, and $\beta$ is the Bohr magneton. When the exchange is very large compared to the dipolar energy, then the linewidth $\Delta H = \Delta a/\gamma$ is proportional to the square of the $\Delta H/d$ divided by the rate of exchange.

\[
\Delta H = 2\rho g^2 \beta S(S+1)^{1/2},
\]

and the exchange field $H_{ex} = a/\gamma$ is given by

\[
H_{ex} = (1.7Jg^2\beta S(S+1)^{1/2},
\]

where $J$ is the exchange integral.

As long as the average distance between the Cu2+ spins remain unchanged, the dipolar and exchange interaction are $T$-independent, giving a line-broadening that is itself independent of temperature when $(g^2/\beta T) \ll 1$. Therefore, the homogeneous broadening predicted by Eq. (3) would be consistent with the temperature and field independent Cu2+ ESR linewidth of Figs. 1 and 2 at high $T$. However, according to Eq. (3), either $\Delta H_{dd}$ should be increased and/or $H_{ex}$ should be decreased by the vacancies in order to explain the enhanced line broadening observed for the argon post-annealed samples (see Figs. 2 and 3). Our results show that the antiferromagnetic transition at $T_N=25$ K is not affected by the post-annealing process, thus we may infer that the exchange field $H_{ex}$ is basically not modified by the level of vacancies present in our samples. Furthermore, in typical cases where the ESR linewidth is strongly narrowed by exchange interaction, the linewidth is expected to diminish at higher magnetic field as a consequence of the so-called 10/3 effect, and this was not observed in our ESR data. Therefore, the increasing of the linewidth for oxygen deficient samples is most likely associated to an increase of $\Delta H_{dd}$ due to the presence of the oxygen vacancies.

In the analysis of our magnetization curves (Fig. 4), we concluded for the argon annealed and single crystal samples of CaCu$_3$Ti$_4$O$_{12}$ the data can be explained by the coexistence of antiferromagnetic coupled Cu2+ spins and a few percent of non-interacting $S=1/2$ spins. Equation (1) yields, for typical cubic paramagnetic salts with average distance between $S=1/2$ like spins of the order of 2–7 Å, to linewidths ranging from 50 to 500 Oe. The Cu2+-Cu2+ distance in cubic CaCu$_3$Ti$_4$O$_{12}$ is about 6 Å. Assuming that the loss of a oxygen atom would transform some of the Cu2+ ions into Cu1+ and, consequently, Ti4+ ions into Ti3+ ($S = 1/2$ ions), the remaining majority of Cu2+ in the vicinity of
a TiO$_6$ octahedron would interact with a Ti$^{3+}$ ($S=1/2$) at an average distance of roughly 3 Å. This new spin configuration would increase the effective homogenous dipolar interaction, however with contribution of dipolar interaction between the unlike Cu$^{2+}$ and Ti$^{3+}$ $S=1/2$ spins and could qualitatively explain the increase of ESR linewidth for the vacancy rich single crystal and argon-annealed sample of CaCu$_3$Ti$_4$O$_{12}$.

Therefore, based on our magnetization data and on the broadening of the Cu$^{2+}$ we can conclude that oxygen vacancy defects in CaCu$_3$Ti$_4$O$_{12}$ are presumably $F^-$ centers. These centers may appear from a trapped electron at a Ti$^{3+}$ eg$(3d_{3z^2-r^2})$ orbital forming a paramagnetic complex.16,17

Now that we have qualitatively described a plausible scenario for the larger Cu$^{2+}$ ESR linewidths in the oxygen deficient CaCu$_3$Ti$_4$O$_{12}$ samples, let us turn to the role played by the oxygen vacancies in the dielectric constants. In Fig. 6 we exemplified how the dielectric constant can be affected by the atmosphere of post-annealing process (upper panel) and by details of the sample preparation method (lower panel). The latter demonstrates how changes in the growth process can influence the value of the dielectric constants that are extrinsic in origin (e.g., associated with grain boundaries and IBLC effect).5,6 However when the sample growth process is maintained the same and as controlled as possible, the dielectric constant is affected by the oxygen vacancies, as are the Cu$^{2+}$ ESR linewidths.

Recently, others have studied the effects of post-annealing in thin films of CaCu$_3$Ti$_4$O$_{12}$ and they have found similar results to those reported here.10 Also, careful studies using transmission electron microscopy have found that grain boundaries are oxygen vacancy richer than the grain interior.23 Thus one may expect that the post-annealing process would create vacancies preferentially at the grain boundary, a fact also reflected in our samples. From the magnetic susceptibility low-T Curie tail (see Fig. 4) one can see that the argon post-annealed polycrystals present a higher number of vacancies than the CaCu$_3$Ti$_4$O$_{12}$ single crystal. However, the single crystals present a broader ESR linewidth than argon post-annealed samples. This result is easily explained by the fact that ESR linewidth arises from ~100% of the Cu$^{2+}$ ions that are predominantly inside the grain. So Cu$^{2+}$ ESR linewidth is more weakly broadened by vacancies present at the grain boundaries. In contrast, for the single crystals, all the vacancies are in the sample bulk, more effectively affecting the Cu$^{2+}$ sites and giving rise to broader linewidths.

Regarding the effect of post-annealing process in $e_0$ for these materials, based on the results mentioned above, one can argue that the effect seen in the upper panel of Fig. 6 is also an extrinsic effect caused by the enhancement of the IBLC affect due to the higher content of vacancies at the grain boundaries. We cannot rule out this scenario but we should point out that this explanation is not valid for the single crystals, and it is certainly bulk vacancy richer as measured by the ESR linewidth.

Also, for the polycrystalline samples, as the ESR linewidth reflects intrinsic properties from inside the grain, and it is not affected by pelletizing the powder on different stages of the growth, the apparent correlation seen in the upper panel of Fig. 6 between the oxygen vacancies, the Cu$^{2+}$ ESR linewidths, and $e_0$ opens the possibility of an intrinsic origin for at least part of the enhanced dielectric constant of these materials. As for the increase in the Cu$^{2+}$ ESR linewidths for oxygen deficient samples, we discussed that oxygen vacancies may create an extra charge near the TiO$_6$ octahedra (tending to drive Ti$^{4+}$ to Ti$^{3+}$). The presence of Ti$^{3+}$ (or an extra charge) can disrupt the TiO$_6$ octahedra placing the Ti atoms in a slightly shifted position with respect to the oxygen cage and allowing for a local electrical polarization to appear.11 Furthermore, paramagnetic complexes arising from Ti$^{3+}$ ions coupled to an oxygen vacancy were experimentally found to occur in ferroelectric materials such as BaTiO$_3$.13,16,17

Therefore the presence of oxygen vacancies in the CaCu$_3$Ti$_4$O$_{12}$ and possible formation of Ti$^{3+}$ could explain the broadening of Cu$^{2+}$ ESR linewidths and shed some light on the origin of the large dielectric constants of ACu$_3$Ti$_4$O$_{12}$. Note that the IBLC and vacancy effects are difficult to separate from each other and in some cases are related. The combination of these effects may account for the conflicting data and interpretations in literature. A conclusive statement about the real intrinsic value $e_0$ for CaCu$_3$Ti$_4$O$_{12}$ requires meticulous quantitative studies of oxygen vacancies, grains sizes, etc., for samples growing in well-controlled process, which is beyond the scope of this work. We concede that our interpretation regarding the role of oxygen vacancies in our ESR and magnetization data is somewhat speculative, and further TiO$_6$ and Cu-site local structure investigation (for instance done by Raman spectroscopy and x-ray absorption in carefully prepared post-annealed samples), would be valuable to confirm our interpretation.

Although studied less frequently, the Cd-based materials also show enhanced broadening of the ESR linewidth for post-argon-annealed samples but the effect is smaller (10–20% broader linewidths for Ar-annealed. samples) than for CaCu$_3$Ti$_4$O$_{12}$. Larger values of $e_0$, attributable to the IBLC effect, were also observed for the Cd samples, but the measured values of the Cd samples were always smaller (at least by a factor of 10) than for CaCu$_3$Ti$_4$O$_{12}$ prepared under the same condition. This result suggests that the Cd sample may be less susceptible to the creation of oxygen vacancies. Finally, we concluded that a single crystal of CaCu$_3$Ti$_4$O$_{12}$ prepared by a traveling-solvent floating zone method behaves such as post argon-annealed polycrystals, suggesting that this crystal is oxygen deficient.

V. CONCLUSIONS

We report experiments of ESR of Cu$^{2+}$ in polycrystalline samples of ACu$_3$Ti$_4$O$_{12}$ (post-annealed in different atmospheres) (A=Ca and Cd). From detailed studies in the Ca-based material we have shown that while the Cu$^{2+}$ ESR g values and the ordering temperature are unaffected by the annealing, the ESR linewidths are dramatically changed by the oxygen content in the sample. Argon post-annealed samples show a much larger linewidth than the O$_2$ or air post-annealed samples. On the other hand, the dielectric constants for these materials were found to be affected by the
oxygen content in the sample as by the details on the sample preparation method. Our results agree with the growing evidence that most of the high value of the dielectric constant reported for CaCu$_3$Ti$_4$O$_{12}$ is due to an extrinsic effect of an internal barrier layer capacitance at grain boundaries but reveal the presence of oxygen vacancy induced Ti$^{3+}$ centers in the bulk of these materials that may contribute to their intrinsic dielectric constant and manifest itself on other interesting physical properties of these materials.

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